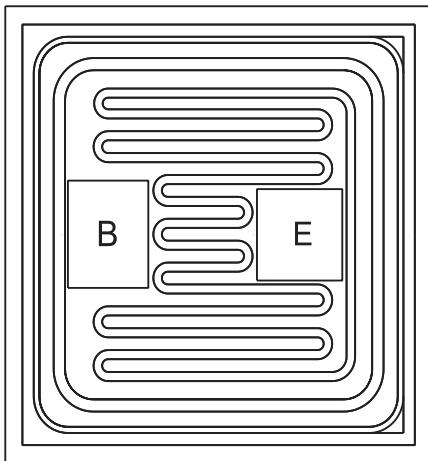


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	26 x 26 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	6.1 x 4.9 MILS
Emitter Bonding Pad Area	5.2 x 5.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

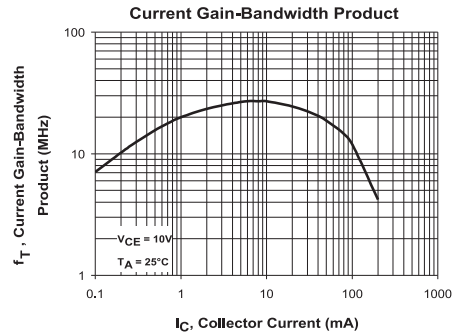
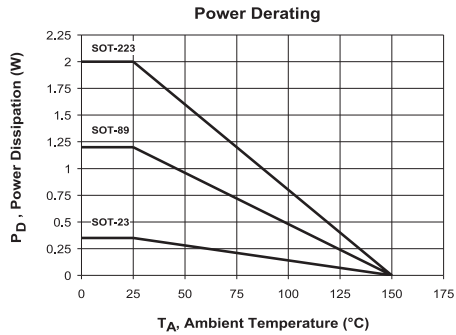
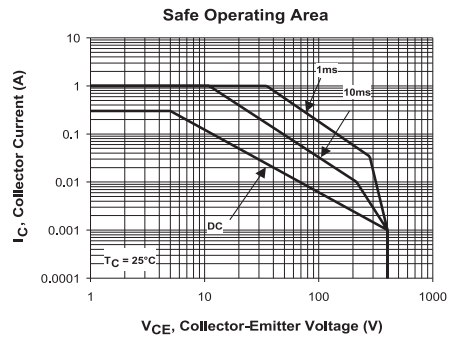
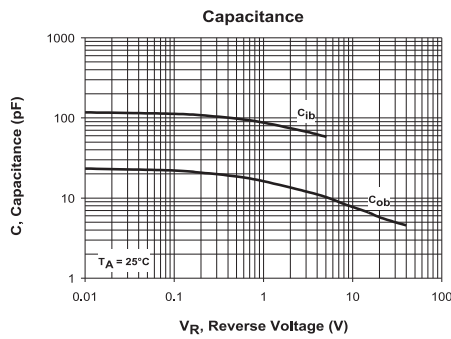
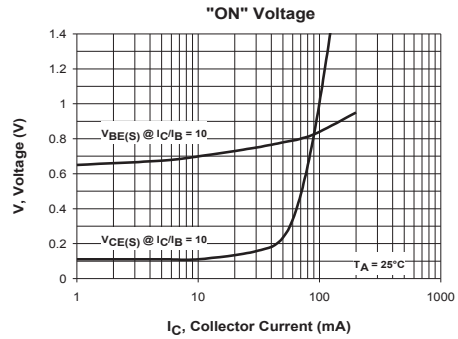
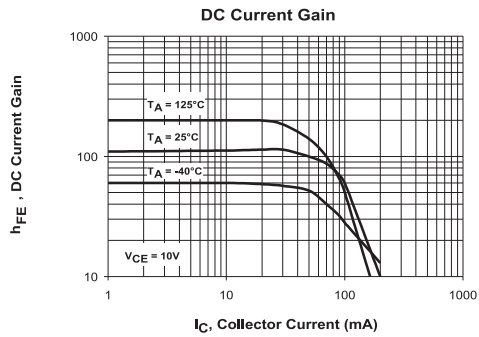
16,880

PRINCIPAL DEVICE TYPES

CMPTA94
CXTA94
CZTA94
MPSA94

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R2 (1-August 2002)



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